

FORM PTO-1449  O I P E DEC 05 2002 CIEP (USE SEVERAL SHEETS IF NECESSARY)	U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMEX.186DV1	APPLICATION NO. 09/764,711
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Raaijmakers et al.	
		FILING DATE January 18, 2001	GROUP 2812

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DR	1.	5,192,708	3/9/93	Beyer et al.	437	90	4/29/92
	2.	5,371,039	12/6/94	Ogaro	437	101	2/18/93
	3.	5,627,092	5/6/97	Alsmeyer et al.	438	152	9/26/94
	4.	5,888,876	3/30/99	Shiozawa et al.	438	386	4/9/94
MR	5.	6,297,088 B1	10/2/01	King	438	243	1/2/00

## FOREIGN PATENT DOCUMENTS

**EXAMINER  
INITIAL**

**OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)**

AR 6. Arienzo et al., "In Situ Arsenic-Doped Polysilicon for VLSI Applications" Transactions on Electron Devices, ED33(1):1535-1538 (1986).

W:\DOCS\ZYW\ZYW-1348.DOC120202

EXAMINER	<i>AL R</i>	DATE CONSIDERED	<i>02/20/03</i>
----------	-------------	-----------------	-----------------